3-PHASE HALF-BRIDGE GATE DRIVER IN SO-28





Description

The DGD23892 is a three-phase gate driver IC designed for highvoltage / high-speed applications, driving N-Channel MOSFETs and IGBTs in a half-bridge configuration. High-voltage processing techniques enable the DGD23892's high-side to switch to 600V in a bootstrap operation.

The DGD23892 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) for easy interfacing with controlling devices and are enabled low to better function in high-noise environments. The driver outputs feature high-pulse current buffers designed for minimum driver cross conduction.

The DGD23892 offers numerous protection functions. A shoot-through protection logic prevents both outputs from being high when both inputs are high (fault state), an undervoltage lockout (UVLO) for V_{CC} shuts down all drivers through an internal fault control, and a UVLO for VBS shuts down the respective high side output. An overcurrent protection will terminate the six outputs. Both the V_{CC} UVLO and the overcurrent protection trip an automatic fault clear with a timing that is adjustable with an external capacitor.

The DGD23892 is offered in SO-28 (Type TH) package and the operating temperature extends from -40°C to +125°C.

Applications

- 3-Phase Motor Inverter Driver
- White Goods Air Conditioner, Washing Machine, Refrigerator
- Industrial Motor Inverter Power Tools, Robotics
- General Purpose 3-Phase Inverter

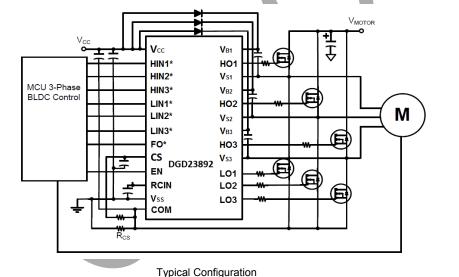
Features

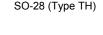
- Three Floating High-Side Drivers in Bootstrap Operation to
- 350mA Source / 650mA Sink Output Current Capability
- Outputs Tolerant to Negative Transients, dV/dt Immune
- Logic Input 3.3V Capability
- Internal Deadtime of 290ns to Protect MOSFETs
- Matched Prop Delay for All Channels
- Outputs Out of Phase with Inputs
- Schmitt Triggered Logic Inputs
- Cross Conduction Prevention Logic
- Undervoltage Lockout for All Channels
- Overcurrent Protection Shuts Down Drivers
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SO-28
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.250 grams (Approximate)







Top View

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DGD23892S28-13	DGD23892	13	24	1,500

- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
 - 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

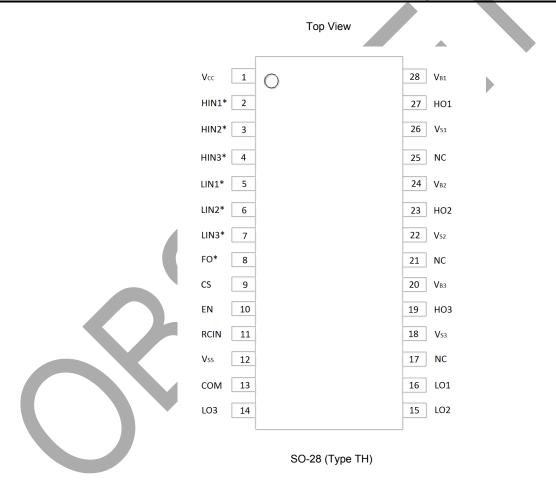


Marking Information



);; = Manufacturer's Marking DGD23892 = Product Type Marking Code YY = Year (ex: 20 = 2020) WW = Week (01 to 53)

Pin Diagrams

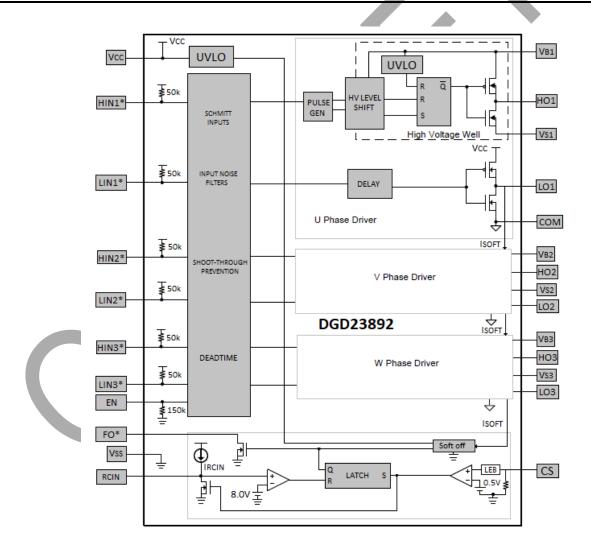




Pin Descriptions

Pin Number	Pin Name	Function	
1	Vcc	Low-Side and Logic Fixed Supply	
2,3,4	HIN1*,HIN2*,HIN3*	Logic Input for High-Side Gate Driver Output, Out of Phase with HO	
5,6,7	LIN1*,LIN2*,LIN3*	Logic Input for Low-Side Gate Driver Output, Out of Phase with LO	
8	FO*	Fault Output with Open Drain (Fault with Overcurrent and V _{CC} UVLO)	
9	CS	Analog Input for Overcurrent Shutdown	
10	EN	Logic Input for Functionality, I/O Logic Functions when EN is High	
11	RCIN	An External RC Network Input used to Define FAULT CLEAR Delay	
12	V_{SS}	Logic Ground	
13	COM	Low-Side Driver Return	
14,15,16	LO3,LO2,LO1	Low-Side Gate Driver Output	
17,21,25	NC	No Connection (No Internal Connection)	
18,22,26	V_{S3}, V_{S2}, V_{S1}	High-Side Floating Supply Return	
19,23,27	HO3,HO2,HO1	High-Side Gate Driver Output	
20,24,28	V_{B3},V_{B2},V_{B1}	High-Side Floating Supply	

Functional Block Diagram





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Supply Voltage	V _B	-0.3 to +618	V
High-Side Floating Supply Offset Voltage	Vs	V _B -18 to V _B +0.3	V
High-Side Floating Output Voltage	V_{HO}	V_S -0.3 to V_B +0.3	V
Low-Side Output Voltage	V_{LO}	-0.3 to V _{CC} +0.3	V
Offset Supply Voltage Transient	dV _S / dt	50	V/ns
Low-Side Fixed Supply Voltage	V _{CC}	-0.3 to +18	V
Logic Input Voltage (HIN*, LIN*, CS, EN and FO*)	V _{IN}	-0.3 to +5.5	V

Thermal Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	P _D	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	60	°C/W
Thermal Resistance, Junction to Case (Note 5)	Rejc	45	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	TL	+300	°C
Storage Temperature Range	T _{STG}	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply Absolute Voltage	V_{B}	V _S + 10	V _S + 15	V
High-Side Floating Supply Offset Voltage	Vs	(Note 6)	600	V
High-Side Floating Output Voltage	V_{HO}	Vs	V _B	V
Low-Side Fixed Supply Voltage	V _{CC}	10	15	V
Low-Side Output Voltage	V_{LO}	COM	V _{CC}	V
Logic Input Voltage (HIN*, LIN*, CS & EN)	V _{IN}	V _{SS}	5	V
Fault Output Voltage	V_{FO}	V _{SS}	V _{CC}	V
Logic Ground	V _{SS}	-5	5	V
Ambient Temperature	T _A	-40	+125	°C

Note: 6. Logic operation for V_S of -5V to +600V.



DC Electrical Characteristics (V_{BIAS} (V_{CC}, V_{BS}) = 15V, @T_A = +25°C, unless otherwise specified.) (Note 7)

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Logic "0" Input Voltage	V _{IH}	2.4	_	_	V	_
Logic "1" Input Voltage	V _{IL}	_	_	8.0	V	_
High Level Output Voltage, V _{BIAS} - V _O	V_{OH}	_		0.1	V	$I_O = 0mA$
Low Level Output Voltage, Vo	V_{OL}	_		0.1	V	$I_O = 0mA$
Offset Supply Leakage Current	I_{LK}	_		10	μΑ	$V_B = V_S = 600V$
Quiescent V _{BS} Supply Current	I_{BSQ}	10	85	130	μΑ	V_{IN} = 0V or 5V, EN = 0V
Quiescent V _{CC} Supply Current	Iccq	_	1.1	1.6	mA	V_{IN} = 0V or 5V, EN = 0V
Logic Input Bias Current (HO=LO=HIGH)	I _{IN+}	_	130	200	μΑ	$V_{IN} = 0V$
Logic Input Bias Current (HO=LO=LOW)	I _{IN-}	_	3.0	20	μΑ	V _{IN} = 5V
Logic Enable "1" Input Bias Current	I _{EN+}	_	50	80	μA	V _{EN} = 5V
Logic Enable "0" Input Bias Current	I _{EN-}	_		2.0	μΑ	V _{EN} = 0V
V _{BS} Supply Undervoltage Positive Going Threshold	V_{BSUV} +	7.6	8.9	9.9	V	
V _{BS} Supply Undervoltage Negative Going Threshold	V_{BSUV-}	7.1	8.3	9.4	V	_
V _{CC} Supply Undervoltage Positive Going Threshold	V _{CCUV+}	7.6	8.9	9.9	V	
V _{CC} Supply Undervoltage Negative Going Threshold	V _{CCUV} -	7.1	8.3	9.4	V	
Output High Short Circuit Pulsed Current	I _{O+}	250	350	-	mA	V _O = 0V, PW ≤ 10µs
Output Low Short Circuit Pulsed Current	I _O -	500	650	_	mA	V _O = 15V, PW ≤ 10μs
Overcurrent Detect Positive Threshold	V_{ITH+}	400	500	600	mV	_
Overcurrent Detect Negative Threshold	V_{ITH}	340	420	500	mV	_
Short-Circuit Input Current	I _{CSIN}	5.0	15	20	μΑ	V _{CSIN} = 1V
RCIN Internal Current Source	I _{RSIN}	6.0	8.0	10	μΑ	_
RCIN Positive Going Threshold Voltage	V _{RCINTH+}	_	8.0	1	V	_
RCIN Negative Going Threshold Voltage (Note 8)	V _{RCINTH} -	_	5.0		V	_
Fault Output Low Level Voltage	V _{FOL}	_	0.2	0.5	V	V _{CS} = 1V, I _{FO} = 1.5mA
RCIN on Resistance	R _{DSRCIN}	40	75	110	Ω	I _{RCIN} = 1.5mA
Fault Output on Resistance	R _{DSFO}	80	130	180	Ω	I _{FO} = 1.5mA

Notes:

- The V_{IN}, V_{TH} and I_{IN} parameters are referenced to V_{SS} and are applicable to all six channels (HIN1*, 2*, 3* and LIN1*, 2*, 3*). The V_O and I_O parameters are applicable to the output pins (HO1, 2, 3 and LO1, 2, 3) and are referenced to COM.
 Guaranteed by design.

AC Electrical Characteristics (V_{BIAS} (V_{CC}, V_{BS}) = 15V, C_L = 1000pF, @T_A = +25°C, unless otherwise specified.)

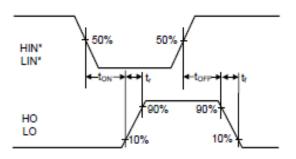
Parameter	Symbol	Min	Тур	Max	Unit	Condition
Turn-On Propagation Delay	ton	200	270	460	ns	$V_S = 0V$
Turn-Off Propagation Delay	toff	200	270	460	ns	$V_S = 0V$
Turn-On Rise Time	t _R	_	40	150	ns	$V_S = 0V$
Turn-Off Fall Time	t _F	_	25	60	ns	V _S = 0V
Delay Matching	t _{DM}	_	_	50	ns	_
Enable Low to Output Shutdown Delay	t _{EN}	225	260	425	ns	_
CS Pin Leading-Edge Blanking Time (Note 9)	t _{BLT}	200	300	400	ns	_
Time from CS Triggering to FO*	t _{FLT}	360	550	760	ns	From V _{CS} = 1V to FO* turn off
Time from CS Triggering to All Gate Outputs Turn Off	t _{ITRIP}	420	615	820	ns	From V _{CS} = 1V to starting gate turn off
Input Filtering Time (HIN*, LIN*, EN)	t _{FLTIN}	_	250	-	ns	_
Fault Clear Time (Note 8)	t _{FLTCLR}	_	3.1	_	ms	C _{RCIN} = 2nF
Deadtime	t _{DT}	200	290	420	ns	_
Deadtime Matching	t _{DTM}	_	_	50	ns	_
Output Pulse Width Matching (Note 10)	t _{PM}	_	50	75	ns	PW _{IN} > 1µs

9. For best performance of CS and FO* in the application, the CS pulse width should be greater than 1.2μs. Notes:

10. t_{PM} is defined as $PW_{IN} - PW_{OUT}$.



Timing Waveforms



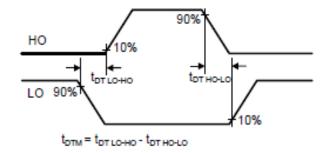


Figure 1. Switching Time Waveform Definitions

Figure 2. Deadtime Waveform Definitions

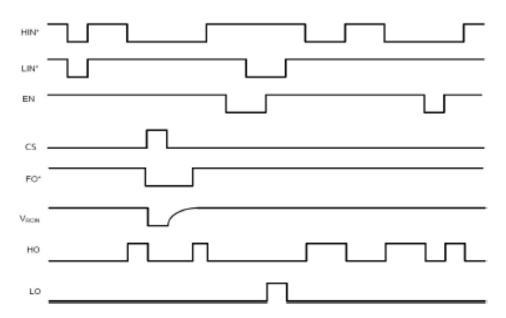


Figure 3. Input/Output Timing Diagram

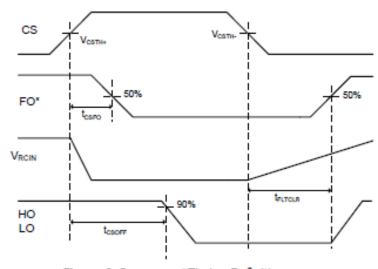


Figure 4. Overcurrent Timing Definitions



Typical Performance Characteristics (@TA = +25°C, unless otherwise specified.)

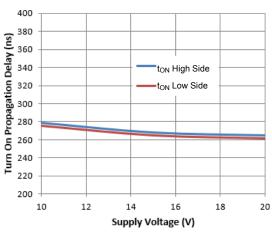


Figure 5. Turn-on Propagation Delay vs. Supply Voltage

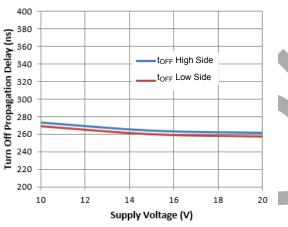


Figure 7. Turn-off Propagation Delay vs. Supply Voltage

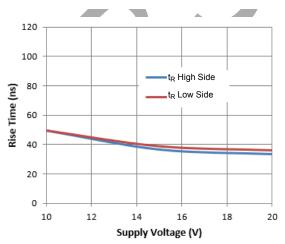


Figure 9. Rise Time vs. Supply Voltage

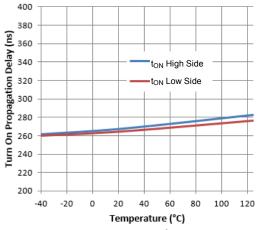


Figure 6. Turn-on Propagation Delay vs. Temperature

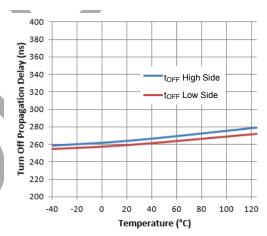


Figure 8. Turn-off Propagation Delay vs. Temperature

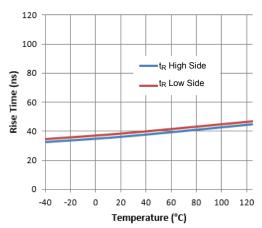


Figure 10. Rise Time vs. Temperature



Typical Performance Characteristics (continued)

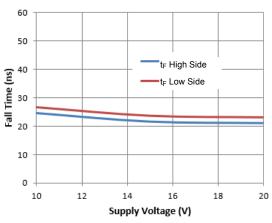


Figure 11. Fall Time vs. Supply Voltage

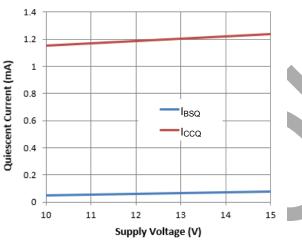


Figure 13. Quiescent Current vs. Supply Voltage

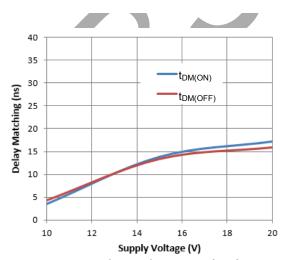


Figure 15. Delay Matching vs. Supply Voltage

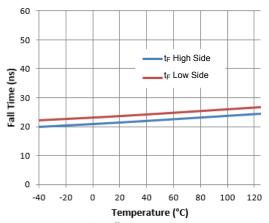


Figure 12. Fall Time vs. Temperature

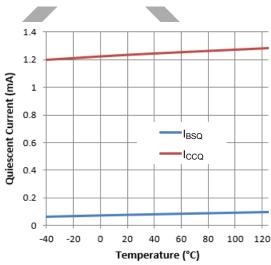


Figure 14. Quiescent Current vs. Temperature

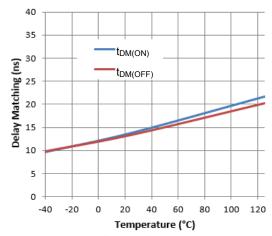


Figure 16. Delay Matching vs. Temperature



Typical Performance Characteristics (continued)

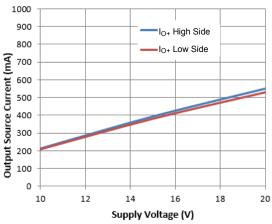
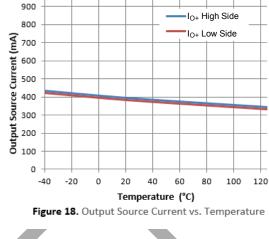


Figure 17. Output Source Current vs. Supply Voltage



1000

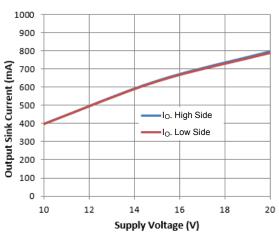


Figure 19. Output Sink Current vs. Supply Voltage

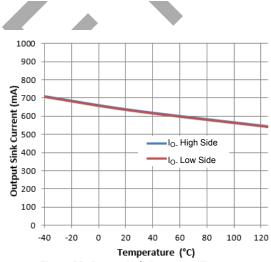


Figure 20. Output Sink Current vs. Temperature

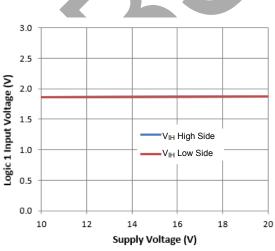


Figure 21. Logic 1 Input Voltage vs. Supply Voltage

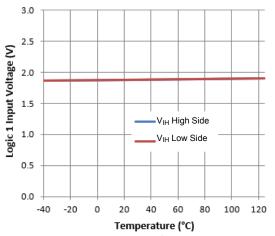


Figure 22. Logic 1 Input Voltage vs. Temperature



Typical Performance Characteristics (continued)

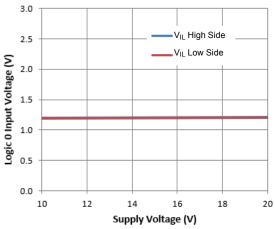


Figure 23. Logic 0 Input Voltage vs. Supply Voltage

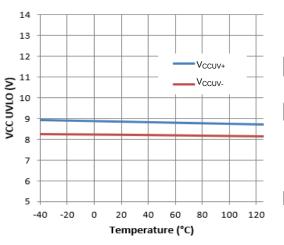
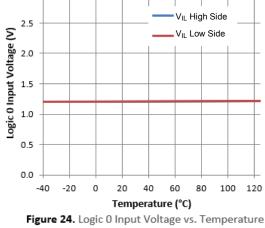


Figure 25. VCC UVLO vs. Temperature



3.0

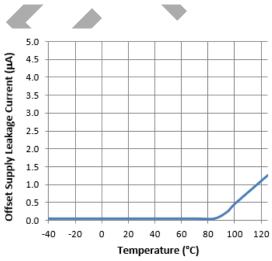


Figure 26. Offset Supply Leakage Current vs. Temperature





Design Notes

Over the past decade, in white goods, there has been a transition from AC motors to brushless DC motors; correspondingly power switching is required to drive the BLDC motors. For even greater efficiency and cost reduction, 3-phase gate driver ICs are used to optimimally drive MOSFETs and IGBTs. The DGD23892, 3-Phase Half-Bridge Gate Driver IC, is a good choice for 3-phase motor applications because of ease of design, reliability, and less space used than 3 x single channel gate driver ICs.

In the inductive 3-phase motor circuit environment, MOSFET/IGBT turn on produces significant current spikes; and the currents are highest and the system is noisiest during startup. In certain applications, with significant noise on the ground lines of V_{SS}-COM (for example during startup), the DGD23892 is susceptible to the noise and can enter fault condition. And if the fault is long enough, the MCU will detect the fault situation, disable inputs and turn off the system. In effect there is a stall at startup. Figure 27 and Figure 28 show startup in a 240V refrigerator compressor application (FO*-MCU (blue) - fault signal at MCU, COM-V_{SS} (yellow) and VS (green) - motor voltage).

This Design Tip will provide two solutions, depending on the current sense circuit, to decrease the IC ground noise and ensure the DGD23892 does not enter fault condition and there is no stall at startup.



Figure 27. During startup when the current is high, COM-V_{SS} noise is high (yellow), fault conditions occur (blue), compressor will eventually stall, 2ms/div



Figure 28. During startup, current is high, COM-V_{SS} noise is high, fault conditions occur, compressor will eventually stall, 100μs/div

Solution 1

If the 3 phase current sensing configuration is similar to Figure 29 or Figure 30, then the best solution is to short the line between V_{SS} and COM directly at the IC. This provides a more stable ground at the IC, and the current sense circuit operates normally (see Figures 31 and 32).

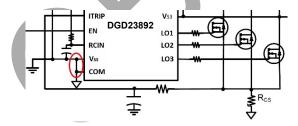


Figure 29. Shorting $V_{SS}\text{-}COM$ at IC for current sense configuration A

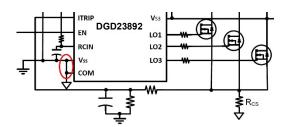


Figure 30. Shorting V_{SS}-COM at IC for current sense configuration B



Design Notes (continued)

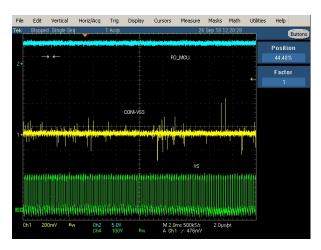


Figure 31. During startup, current is high, with shorted COM-V_{SS}, noise is less, fault conditions do not occur, compressor will not stall, 2ms/div



Figure 32. During startup, current is high, with shorted COM- V_{SS} , noise is less, fault conditions do not occur, compressor will not stall, $100\mu s/div$

Solution 2

If the 3-phase current sensing configuration is similar to Figure 33, then the best solution is to add a ceramic capacitor $(0.022 - 0.1 \mu F)$ between V_{SS} and COM directly at the IC. This provides a more stable ground at the IC, and the current sense circuit operates normally (see Figures 34 and 35)

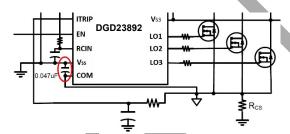


Figure 33. Adding capacitor between V_{SS} -COM at IC for current sense configuration C

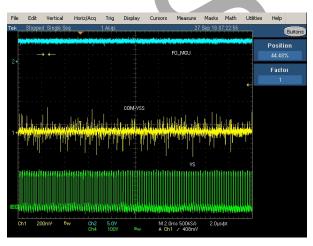


Figure 34. During startup current is high, with cap between COM- V_{SS} , noise is less, fault conditions do not occur, compressor will not stall, 2ms/div

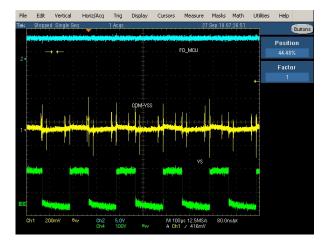


Figure 35. During startup current is high, with cap between COM- V_{SS} , noise is less, fault conditions do not occur, compressor will not stall, 100us/div

Summary

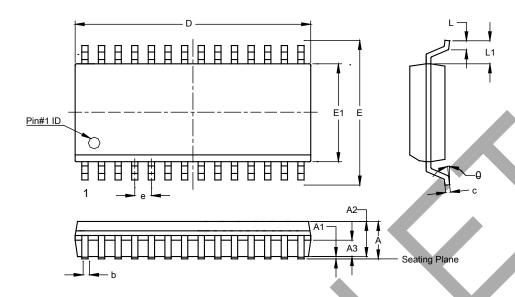
To improve the performance of the DGD23892 during high current operation of 3-phase motor applications, it is best to make a more stable IC ground. Depending on the current sense circuit arrangement in the 3-phase motor driver application, two solutions are provided: one that shorts the connection between COM- V_{SS} and another is adding a ceramic capacitor between COM- V_{SS} . In a compressor application, there were no fault conditions seen at the MCU and the COM- V_{SS} noise was significantly less with the solutions provided.



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-28 (Type TH)

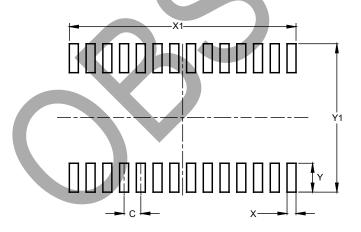


SO-28 (Type TH)						
Dim	Min	Max	Тур			
Α	-	2.65				
A1	0.10	0.30				
A2	2.25	2.35	2.30			
A3	0.97	1.07	1.02			
b	0.39	0.48				
С	0.25	0.31				
D	17.80	18.20	18.00			
Е	10.10	10.50	10.30			
E1	7.30	7.70	7.50			
е	e 1.27 BSC					
L	0.70	1.00				
L1	1.40 BSC					
θ	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-28 (Type TH)



Dimensions	Value (in mm)		
С	1.270		
Х	0.680		
X1	17.190		
Υ	2.200		
Y1	11.300		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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